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	D. AKAI ET AL, Science d Direct, "Epitaxial Growth of Pt(001) thin films on Si substrates using an epitaxial γ-A1 ₂ O ₃ (001) buffer layer, Journal of Crystal Growth 264 (2004) 463-467								
	D. AKAI, APPLIED PHYSICS LETTERS 86, 202906 (2005), Ferroelectric properties of sol-gel delivered epitaxial Pb(Zrx,								
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